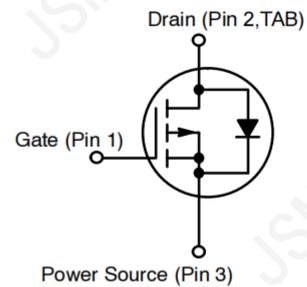


**Description:**

This P-Channel MOSFET uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. It can be used in a wide variety of applications.


**TO-263**
**Features:**

- ◆  $V_{DS}=-60V, I_D=-65A, R_{DS(ON)}<20m\Omega@V_{GS}=-10V$
- ◆ Low gate charge.
- ◆ Green device available.
- ◆ Advanced high cell density trench technology for ultra low  $R_{DS(ON)}$ .
- ◆ Excellent package for good heat dissipation.


**Absolute Maximum Ratings:** ( $T_C=25^\circ C$  unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current- $T_C=25^\circ C$	-65	A
	Continuous Drain Current- $T_C=100^\circ C$	-45	A
$I_{DM}$	Pulsed Drain Current <sub>1</sub>	-280	A
$P_D$	Total Power Dissipation	280	W
$E_{AS}$	Single Pulsed Avalanche Energy	750	mJ
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55to+150	$^\circ C$

**Thermal Characteristics:**

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.44	$^\circ C/W$

**Electrical Characteristics:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-60V$	---	---	-1	$\mu A$
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.1	-1.6	-2.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-20A$	---	16.5	20	m $\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	---	18.5	22	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=-20V, V_{GS}=0V, f=1\text{MHz}$	---	4399	---	pF
$C_{oss}$	Output Capacitance		---	258	---	
$C_{rss}$	Reverse Transfer Capacitance		---	211	---	
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=-30V, I_D=-20A, V_{GS}=-10V$ $R_G=1\Omega$	---	23	---	ns
$t_r$	Rise Time		---	17	---	ns
$t_{d(off)}$	Turn-Off Delay Time		---	55	---	ns
$t_f$	Fall Time		---	29	---	ns
$Q_g$	Total Gate Charge		$V_{GS}=-10V, V_{DS}=-30V, I_D=-20A$	---	114	---
$Q_{gs}$	Gate-Source Charge	---		27.3	---	nC
$Q_{gd}$	Gate-Drain "Miller" Charge	---		49	---	nC
<b>Drain-Source Diode Characteristics</b>						
$V_{SD}$	Drain Diode Forward Voltage	$V_{GS}=0V, I_S=-20A$	---	---	-1.2	V
$I_S$	Continuous Source Current	$V_G=V_D=0V$	---	---	-65	A
$I_{SM}$	Pulsed Source Current		---	---	-280	A
$T_{rr}$	Reverse Recovery Time	$T_J=25^\circ\text{C}, I_F=-20A,$	---	117	---	nS
$Q_{rr}$	Reverse Recovery Charge	$di/dt=100A/\mu s$	---	420	---	nC

**Notes:**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition:  $T_J=25^\circ\text{C}, V_{DD}=-25V, V_G=-5V, R_G=25\Omega, L=0.5\text{mH}, I_{AS}$
3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

Typical Characteristics: ( $T_c=25^\circ\text{C}$  unless otherwise noted)

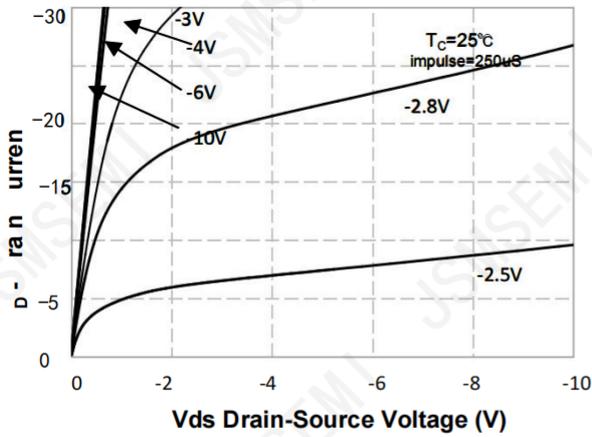


Figure 1. On-Region Characteristics

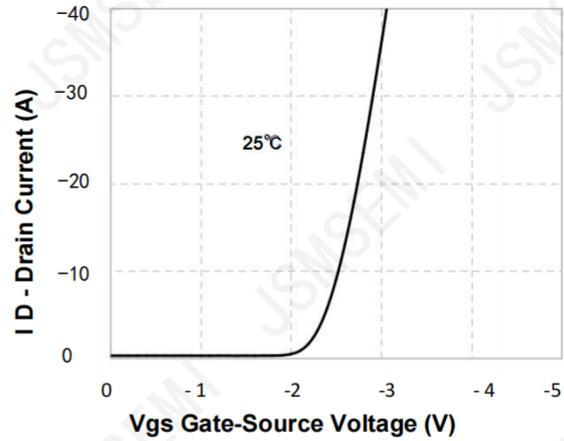


Figure 2. Transfer Characteristics

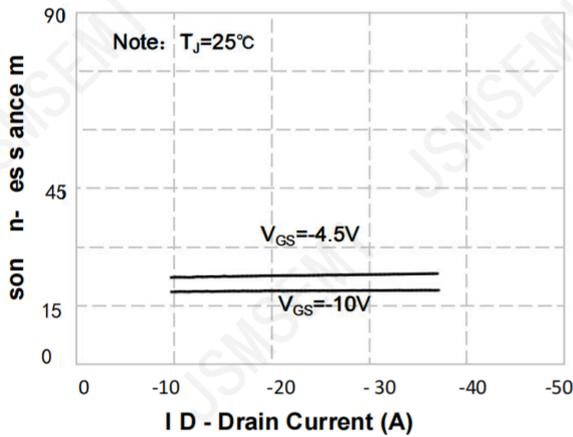


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

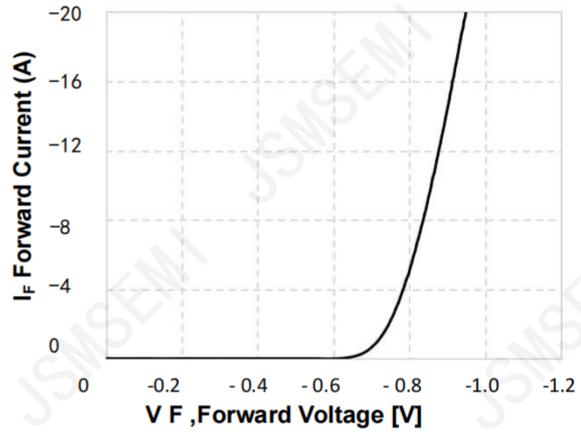


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

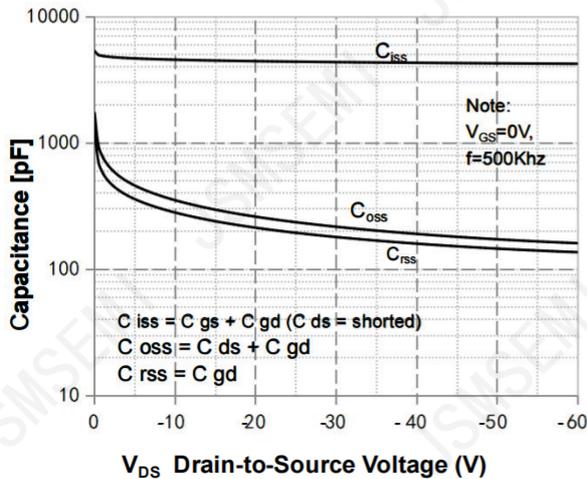


Figure 5. Capacitance Characteristics

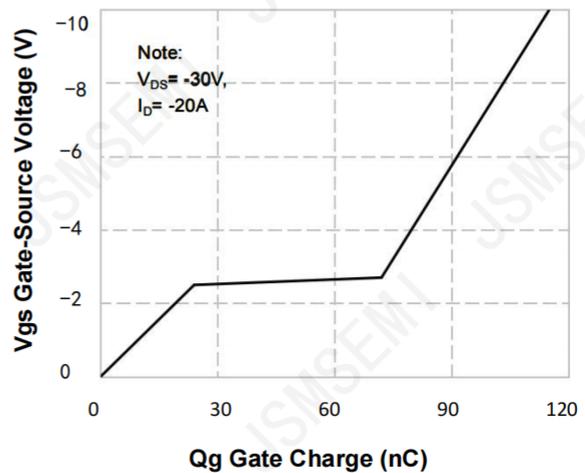


Figure 6. Gate Charge Characteristics

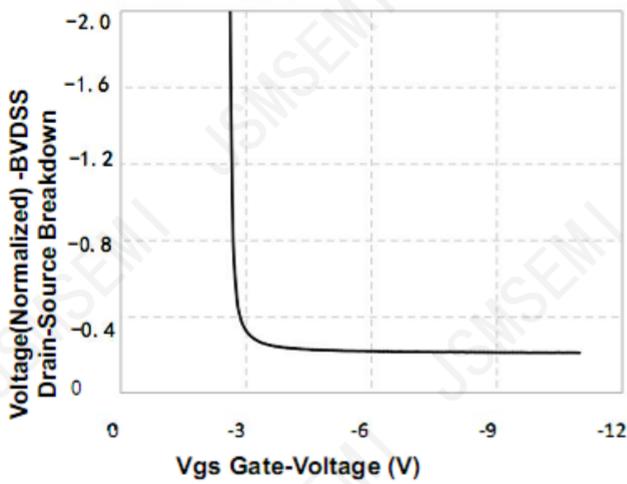


Figure 7. Breakdown Voltage Variation vs Gate-Voltage

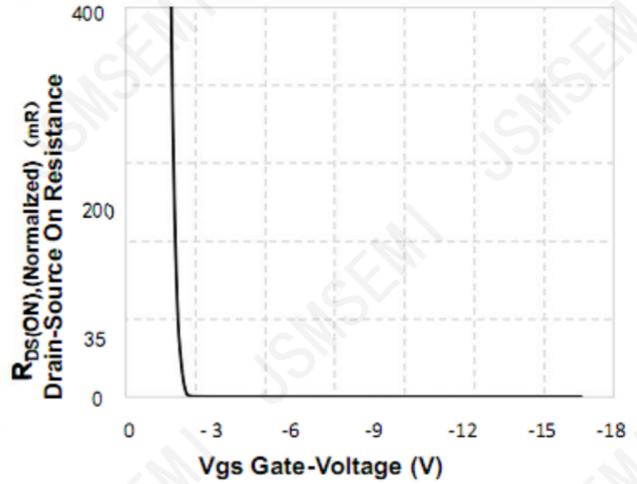


Figure 8. On-Resistance Variation vs Gate Voltage

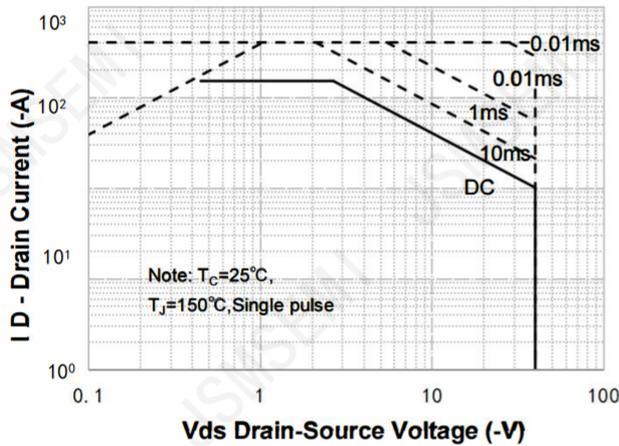


Figure 9. Maximum Safe Operating Area

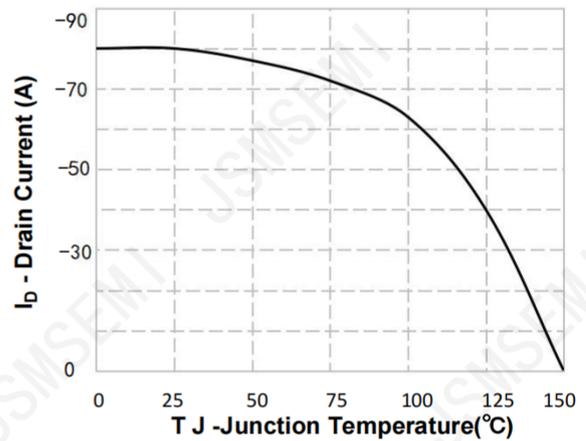


Figure 10. Maximum Continuous Drain Current vs Case Temperature

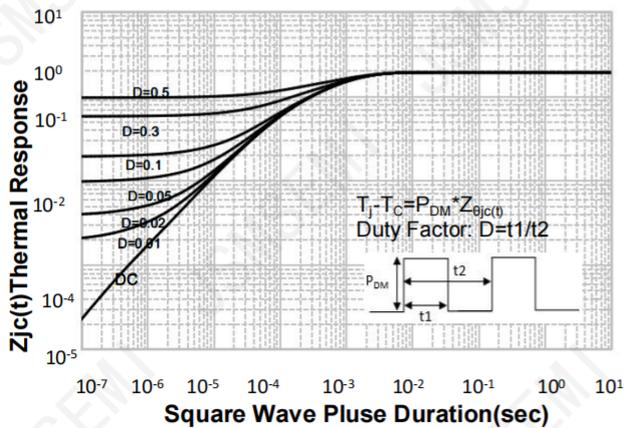
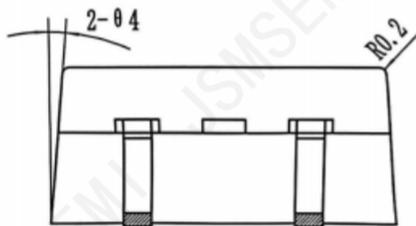
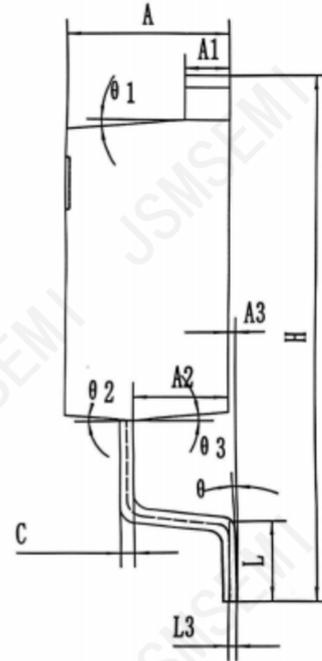
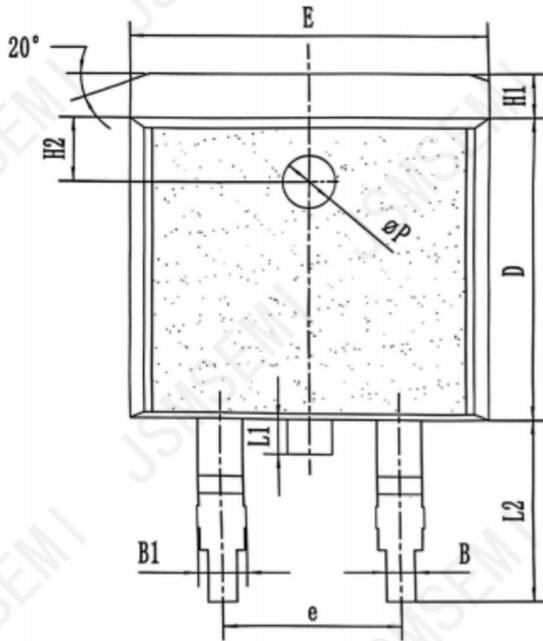


Figure 11. Transient Thermal Response Curve

## Package Information

TO-263

Unit: mm



COMMON DIMENSIONS			
SYMBOL	MM		
	MIN	NOM	MAX
*A	4.50	4.60	4.70
*A1	1.22	1.27	1.32
A2	2.57	2.67	2.77
*A3	0.00		0.20
*B	0.76	0.81	0.87
B1	1.32	1.37	1.42
*C	0.33	0.38	0.43
*D	8.55	8.65	8.75
*e	5.08 BSC		
*E	10.06	10.16	10.26
*H	14.80	15.00	15.20
H1	1.17	1.27	1.37
H2	1.85 REF		
*L	2.09	2.39	2.69
L1	0.80	1.00	1.20
L2	4.88	5.08	5.28
L3	0.25 REF		
φP	1.40	1.50	1.60
θ	0°		8°
θ1	3°	5°	7°
θ2	3°	5°	7°
θ3	3°	5°	7°
θ4	3°	5°	7°

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## Revision History

Rev.	Change	Date
V1.0	Initial version	2/23/2024

## Important Notice

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